

P-Channel Enhancement Mode MOSFET

Feature

Pin Description

- -30V/-65A
R_{DS(ON)} = 7.9 m (typ.) @V_{GS} = -10V
R_{DS(ON)} = 13 m (typ.) @V_{GS} = -4.5V

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Absolute Maximum Ratings

Symbol	Parameter		Rating	Unit
Common Ratings (Tc=25°C Unless Otherwise Noted)				
V _{DSS}	Drain-Source Voltage		-30	V
V _{GSS}	Gate-Source Voltage		±20	V
T _J	Junction Temperature Range		-55 to 175	°C
T _{STG}	Storage Temperature Range			°C
I _S	Source Current-Continuous(Body Diode)	Tc=25°C	-65	A
Mounted on Large Heat Sink				
I _{DM}	Pulsed Drain Current *	Tc=25°C	-195	A
I _D	Continuous Drain Current	Tc=25°C	-65	A
		Tc=100°C	-46	A
P _D	Maximum Power Dissipation	Tc=25°C	75	W
		Tc=100°C	37.5	W
R _{θJC}	Thermal Resistance, Junction-to-Case		2.01	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient **		75	°C/W
E _{AS}	Single Pulsed-Avalanche Energy ***	L=0.3mH	116	mJ

Note: * Repetitive rating; pulse width limited by max.junction temperature.

** Surface mounted on 1in2 FR-4 board.

*** Limited by T_{Jmax}, starting T_J=25°C, L = 0.3mH, R_G= 25Ω, V_{GS} = -10V.

Electrical Characteristics(Tc =25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	HYG110P03LQ1			Unit
			Min	Typ.	Max	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =-250μA	-30	-	-	V
I _{DSS}	Drain-to-Source Leakage Current	V _{DS} =-30V, V _{GS} =0V	-	-	-1	μA
		T _J =125°C	-	-	-50	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =-250μA	-1.0	-1.6	-3.0	V
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ± 20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =-10V, I _{DS} =-20A	-	7.9	9.9	mΩ
		V _{GS} =-4.5V, I _{DS} =-20A	-	13	1	

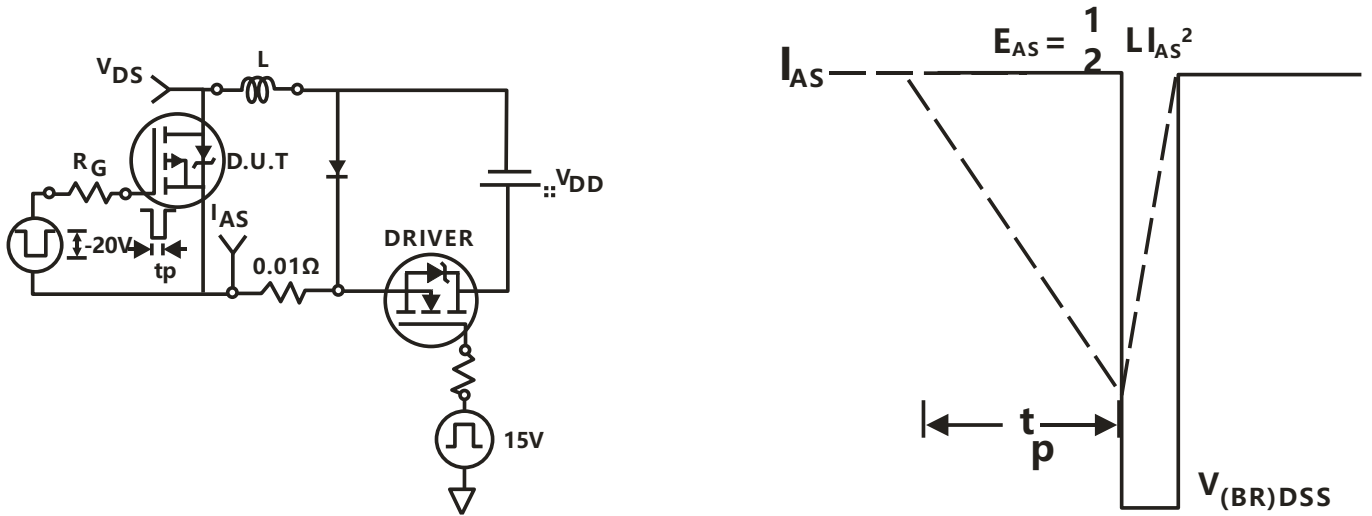
Electrical Characteristics (Cont.) (T_c =25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	HYG110P03LQ1			Unit
			Min	Typ.	Max	
Dynamic Characteristics						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	-	5.9	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-25V, Frequency=1MHz	-	2030	-	pF
C _{oss}	Output Capacitance		-	247	-	
C _{rss}	Reverse Transfer Capacitance		-	222	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =-15V, R _G =2.5 Ω, I _{DS} =-20A, V _{GS} =-10V	-	8.9	-	ns
T _r	Turn-on Rise Time		-	60.9	-	
t _{d(OFF)}	Turn-off Delay Time		-	65.3	-	
T _f	Turn-off Fall Time		-	76.4	-	
Gate Charge Characteristics						
Q _g	Total Gate Charge(V _{GS} =-10V)	V _{DS} =-24V, I _{DS} =-20A	-	47.1	-	nC
	Total Gate Charge(V _{GS} =-4.5V)		-	24.1	-	
Q _{gs}	Gate-Source Charge		-	7.9	-	
Q _{gd}	Gate-Drain Charge		-	13.3	-	
V _{plateau}	Gate plateau voltage		-	-3.5	-	V

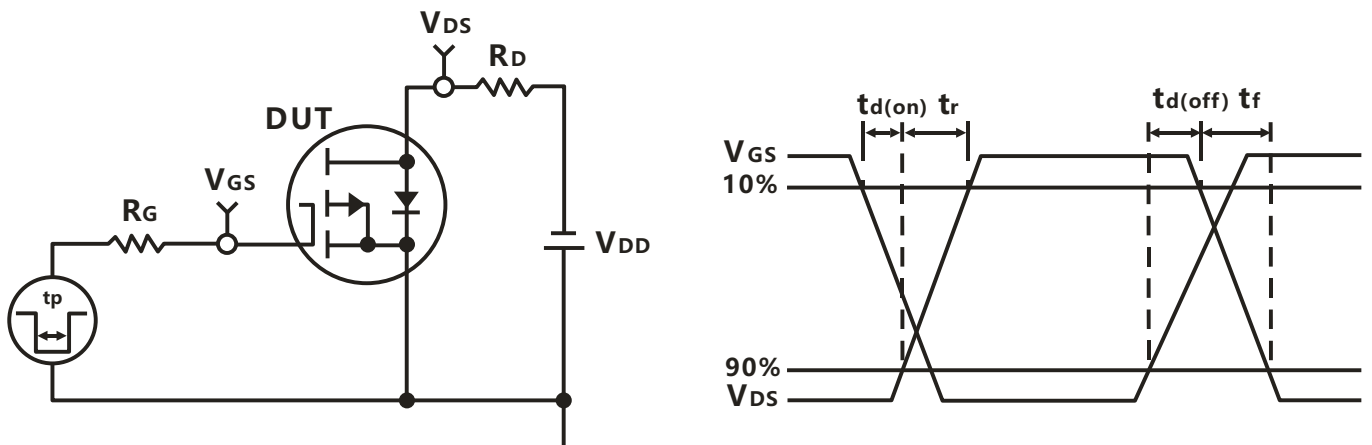
Note: *Pulse test, pulse width 300us, duty cycle 2%

Typical Operating Characteristics(Cont.)

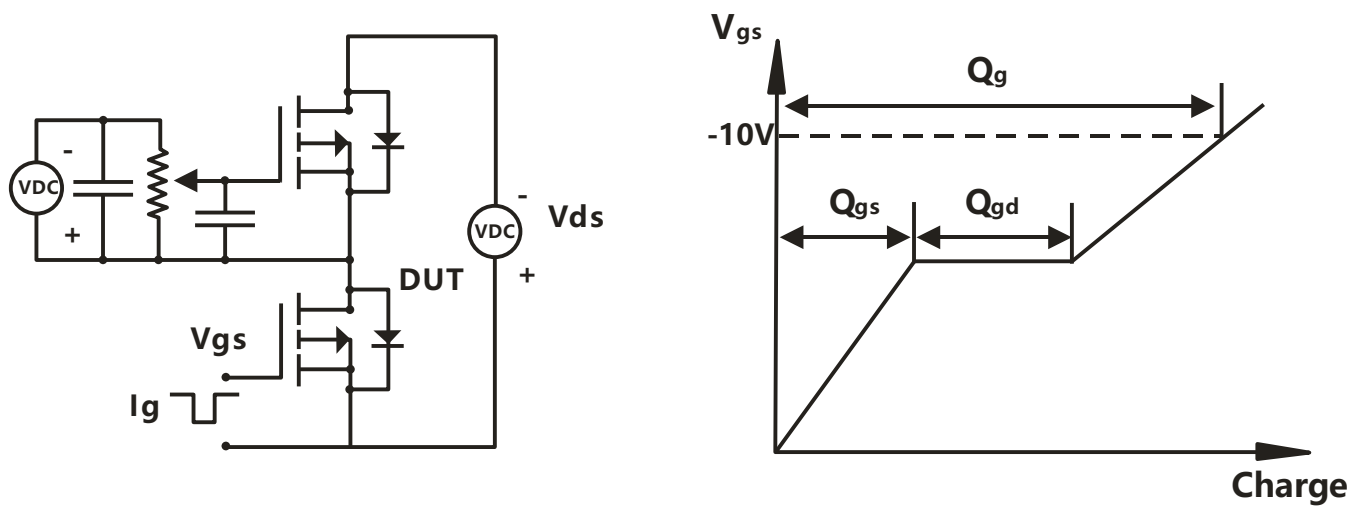
Avalanche Test Circuit



Switching Time Test Circuit



Gate Charge Test Circuit



Device Per Unit

Package Type	Unit	Quantity
TO-252-2L	Tube	75
TO-252-2L	Reel	2500
TO-251-3L	Tube	75
TO-251-3S	Tube	75

Package Information

TO-252-2L

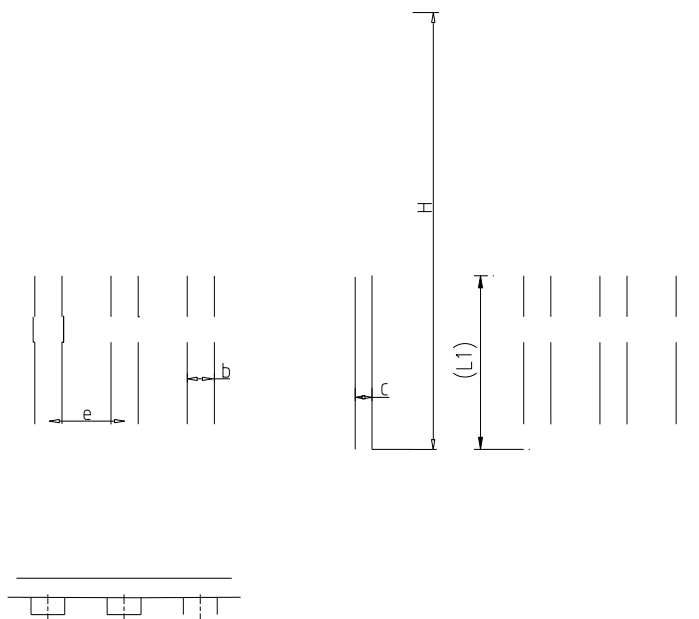
COMMON DIMENSIONS			
SYMBOL	mm		
	MIN	NOM	MAX
A	2.20	2.30	2.40
A1	0.00	-	0.12
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b3	5.20	5.33	5.46

c

TO-251-3L

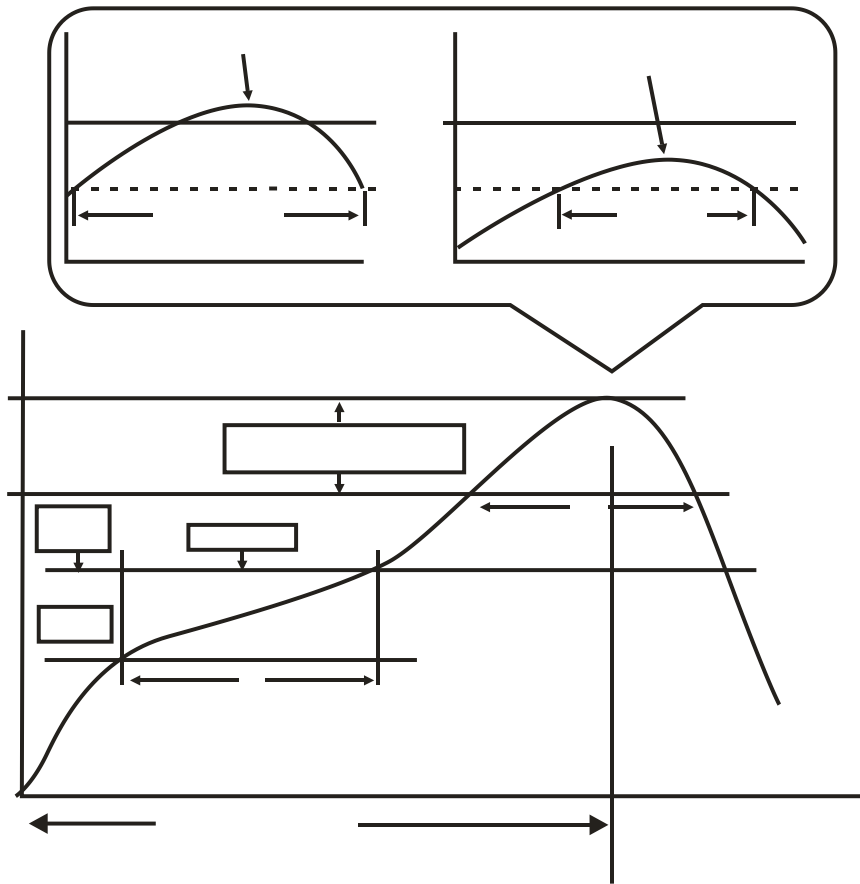
COMMON DIMENSIONS			
SYMBOL	mm		
	MIN	NOM	MAX
A	2.20	2.30	2.38
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b2	0.00	0.04	0.10
b2'	0.00	0.04	0.10
b3	5.20	5.33	5.46
c	0.43	0.53	0.61
D	5.98	6.10	6.22
D1	4.30	5.30	

TO-251-3S



COMMON DIMENSIONS			
SYMBOL	mm		
	MIN	NOM	MAX
A	2.20	2.30	2.38
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b3	5.20	5.33	5.46
c	0.43	0.53	0.60
D	5.98	6.10	6.22
D1	5.30REF		
E	6.40	6.60	6.73
E1	4.63	-	-
e	2.286BSC		
H	10.00	11.22	11.44
L1	3.90	4.10	4.30
L3	0.88	1.02	1.28
L5	1.65	1.80	1.95

Classification Profile



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T _{min})	100 °C	150 °C
Temperature max (T _{max})	150 °C	200 °C
Time (T _{min} to T _{max}) (t _s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T _{soak} to T _p)	3 °C/second max.	3°C/second max.
Liquidous temperature (T _L)	183 °C	217 °C
Time at liquidous (t _L)	60-150 seconds	60-150 seconds
Peak package body Temperature (T _p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t _p)** within 5°C of the specified classification temperature (T _c)	20** seconds	30** seconds
Average ramp-down rate (T _p to T _{max})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
*Tolerance for peak profile Temperature (T _p) is defined as a supplier minimum and a user maximum.		
** Tolerance for time at peak profile temperature (t _p) is defined as a supplier minimum and a user maximum.		

Table 1.SnPb Eutectic Process – Classification Temperatures (Tc)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
2.5 mm	220 °C	220 °C

Table 2.Pb-free Process – Classification Temperatures (Tc)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ ≥2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HTRB	JESD-22, A108	168/500 Hrs, Bias @ 150°C
HTGB	JESD-22, A108	168/500 Hrs, V _{gs} 100% @ 150°C
PCT	JESD-22, A102	96 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	250/500 Cycles, -55°C~150°C

Customer Service

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